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Inventor: Kie Y. Ahn et al.

Title: Highly Reliable Stacked Amorphous Gate Oxides and Devices Formed

Therewith

Assignee: Micron Technology, Inc.

S. Staver  
DA  
10-29-01

**INFORMATION DISCLOSURE STATEMENT**

References -- See Attached Form PTO-1449

The attached form PTO-1449 is submitted in compliance with 37 CFR §1.56.  
Copies of documents listed on the Form PTO-1449 are enclosed, except that copies of the listed pending applications are not enclosed.

No admission is made regarding whether all the submitted references are prior art.

Respectfully submitted,

Dated: June 18, 2001

Inventor: Kei Y. Ahn  
Kie Y. Ahn

Dated: \_\_\_\_\_

Inventor: \_\_\_\_\_  
Leonard Forbes

Dated: Aug 28, 2001

Attorney: Bernard Berman  
Bernard Berman  
Reg. No.: 37,279

Inventor: Kie Y. Ahn et al.

Title: A Dielectric Layer Forming Method and Devices Formed Therewith

Assignee: Micron Technology, Inc.



**INFORMATION DISCLOSURE STATEMENT**

References -- See Attached Form PTO-1449

The attached form PTO-1449 is submitted in compliance with 37 CFR §1.56. Copies of documents listed on the Form PTO-1449 are enclosed, except that copies of the listed pending applications are not enclosed.

No admission is made regarding whether all the submitted references are prior art.

Respectfully submitted,

Dated: \_\_\_\_\_

Inventor: \_\_\_\_\_  
Kie Y. Ahn

Dated: 1 June 2001

Inventor: *Leonard Forbes*  
Leonard Forbes

Dated: Aug 28 2001

Attorney: *Bernard Berman*  
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